

英飞凌汽车级100V 175°C N沟道增强型

OptiMOS™ 5 功率晶体管



特点

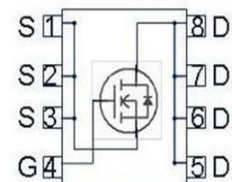
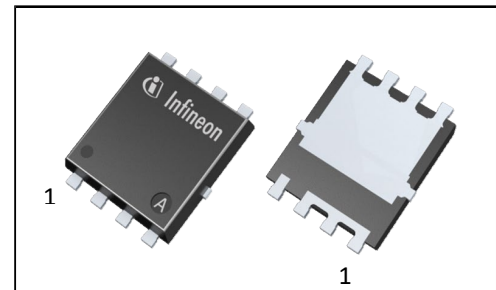
- 适用于汽车应用的功率MOSFET
- N 沟道 - 增强型 - 逻辑电平
- MSL1 回流焊峰值温度高达 260°C
- 工作温度 175°C
- 绿色产品：符合 RoHS 标准
- 100% 雪崩测试

Type	Package	Marking
IAUC100N10S5L054	PG-TDSON-8-34	5N10L054

产品概述

V_{DS}	100	V
$R_{DS(on),max}$	5.4	mΩ
I_D	100	A

PG-TDSON-8-34



除非另有规定，否则均为 $T_j=25^\circ\text{C}$ 的**最大额定值**。

Parameter	Symbol	Conditions	Value	Unit
Drain current	I_D	$V_{GS}=10\text{ V}$, Chip limitation ^{1,2)}	101	A
		$V_{GS}=10\text{ V}$, DC current ³⁾	100	
		$T_a=85^\circ\text{C}$, $V_{GS}=10\text{ V}$, R_{thJA} on 2s2p ^{2,4)}	17	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_c=25^\circ\text{C}$	400	
Avalanche energy, single pulse ²⁾	E_{AS}	$I_D=50\text{ A}$	64	mJ
Avalanche current, single pulse	I_{AS}	-	52	A
Gate source voltage	V_{GS}	-	± 20	V
Power dissipation	P_{tot}	$T_c=25^\circ\text{C}$	130	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C

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Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

热特性²⁾

Thermal resistance, junction - case	R_{thJC}	-	-	-	1.15	K/W
Thermal resistance, junction - ambient ⁴⁾	R_{thJA}	-	-	23.8	-	

除非另有规定，否则均为 $T_j=25^\circ\text{C}$ 的**电气特性**。

静态参数特性

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1mA$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=64\mu A$	1.2	1.7	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V, T_j=25^\circ\text{C}$	-	0.1	1	μA
		$V_{DS}=100V, V_{GS}=0V, T_j=125^\circ\text{C}^{2)}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=50A$	-	6.0	8.1	m Ω
		$V_{GS}=10V, I_D=50A$	-	4.6	5.4	
Gate resistance ²⁾	R_G	-	-	1.4	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

动态参数特性²⁾

Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=50V,$ $f=1MHz$	-	2880	3744	pF
Output capacitance	C_{oss}		-	465	605	
Reverse transfer capacitance	C_{rss}		-	23	35	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50V, V_{GS}=10V,$ $I_D=50A, R_{G,ext}=3.5\Omega$	-	5	-	ns
Turn-off delay time	$t_{d(off)}$		-	23	-	
Rise time	t_r		-	3	-	
Fall time	t_f		-	13	-	

栅极电荷特性²⁾

Gate to source charge	Q_{gs}	$V_{DD}=50V, I_D=50A,$ $V_{GS}=0 \text{ to } 10V$	-	9	12	nC
Gate to drain charge	Q_{gd}		-	7	11	
Gate charge total	Q_g		-	41	53	
Gate plateau voltage	$V_{plateau}$		-	3.2	-	V

反向二极管

Diode continuous forward current ²⁾	I_S	$T_C=25^\circ C$	-	-	100	A
Diode pulse current ²⁾	$I_{S,pulse}$	$T_C=25^\circ C$	-	-	400	
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_F=50A,$ $T_J=25^\circ C$	-	0.9	1.1	V
Reverse recovery time ²⁾	t_{rr}	$V_R=50V, I_F=50A,$	-	49	-	ns
Reverse recovery charge ²⁾	Q_{rr}	$di_F/dt=100A/\mu s$	-	65	-	

¹⁾ 实际上，电流能力受到包括客户特定的印刷电路板在内的整体系统设计的限制。

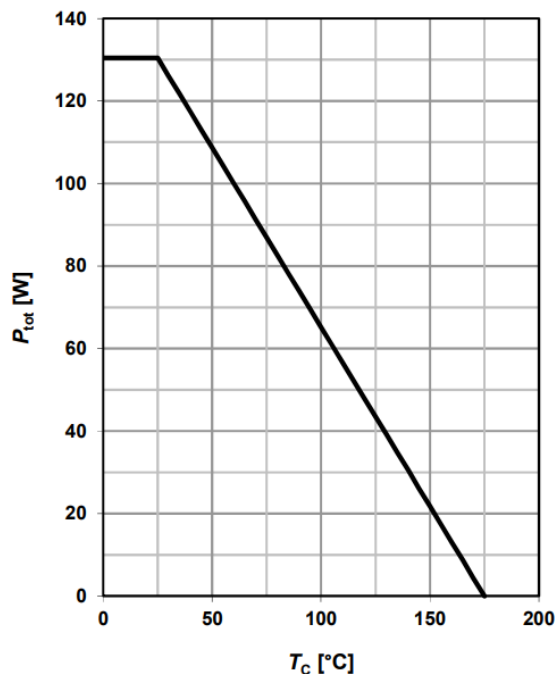
²⁾ 这些参数不经过生产测试，但经过设计和/或特性验证。

³⁾ 本产品可根据最佳实践在指定电流下运行，以尽量减少焊点处的电迁移。在罕见情况或电流浪涌时，可能会超过该值。

⁴⁾ 器件放置于根据JEDEC标准 (JESD51-5-7) 定义的 2s2p FR4 印刷电路板上。印刷电路板垂直放置在静止空气中。

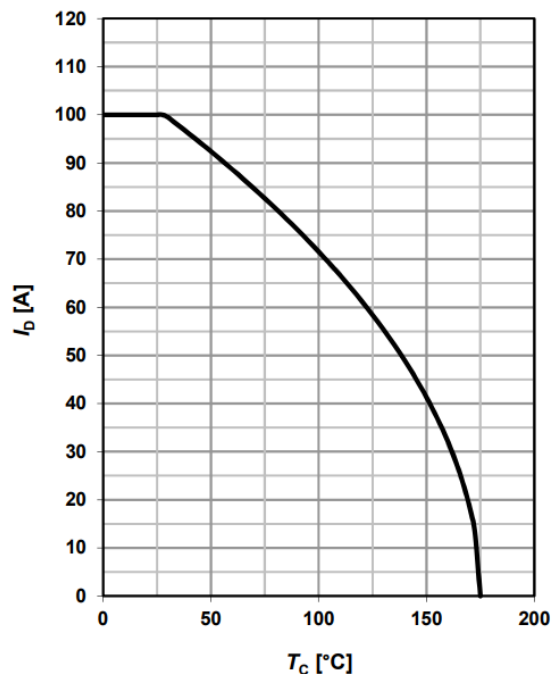
1 功率耗散

$$P_{\text{tot}} = f(T_c); V_{\text{GS}} = 10 \text{ V}$$



2 漏极电流

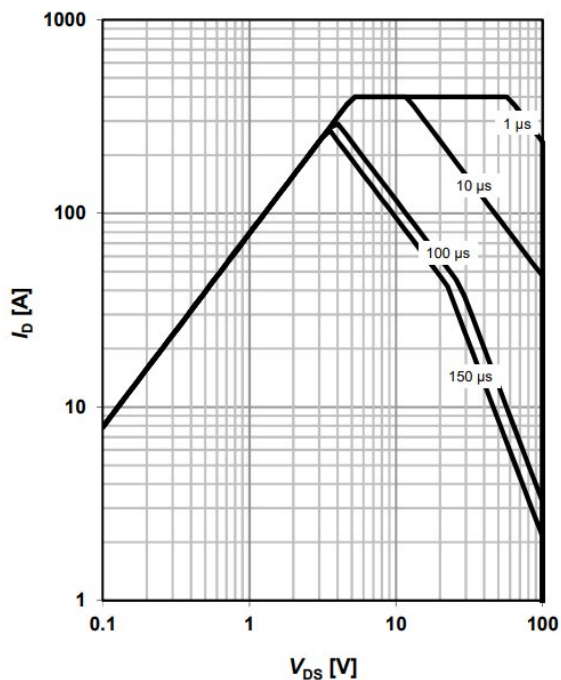
$$I_D = f(T_c); V_{\text{GS}} = 10 \text{ V}$$



3 安全工作区

$$I_D = f(V_{\text{DS}}); T_c = 25^\circ\text{C}; D = 0$$

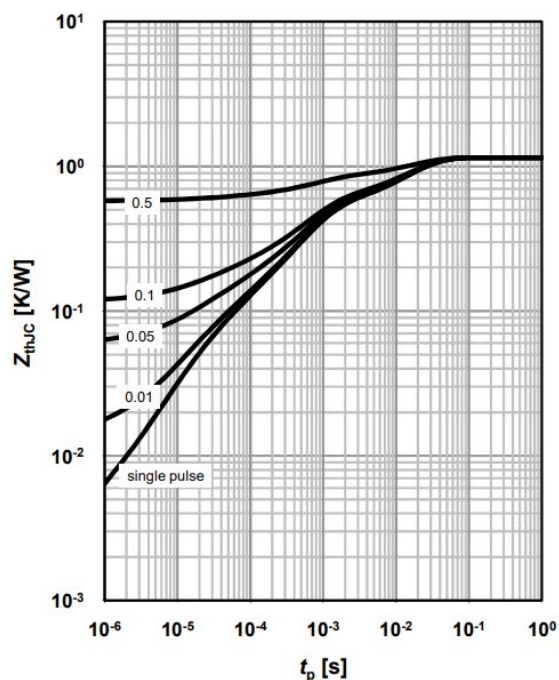
parameter: t_p



4 最大瞬态热阻抗

$$Z_{\text{thJC}} = f(t_p)$$

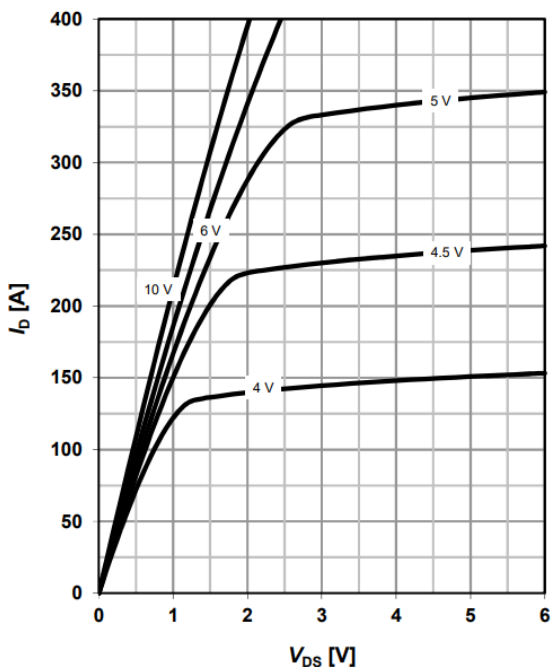
parameter: $D = t_p/T$



5 典型输出特性

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

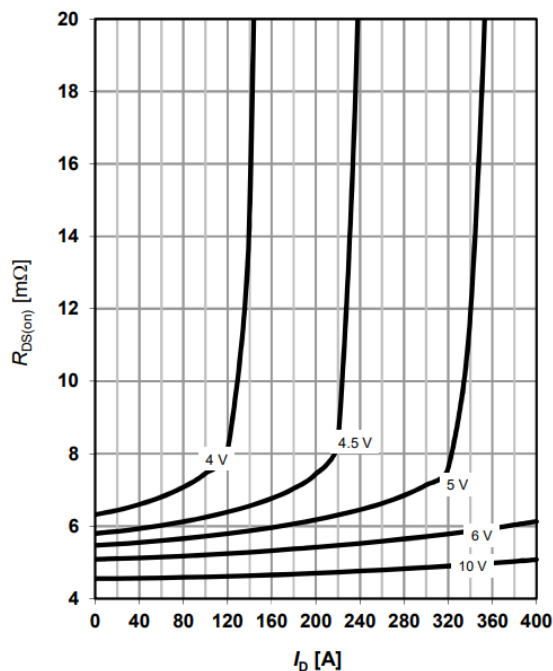
parameter: V_{GS}



6 典型漏源导通电阻

$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

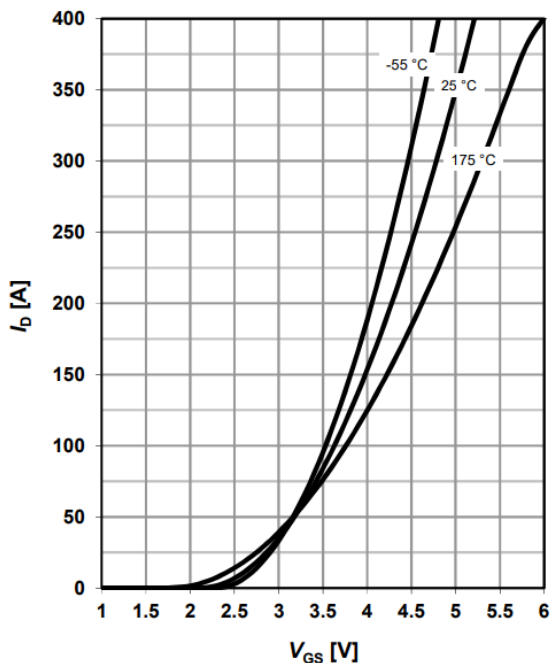
parameter: V_{GS}



7 典型转移特性

$$I_D = f(V_{GS}); V_{DS} = 6\text{V}$$

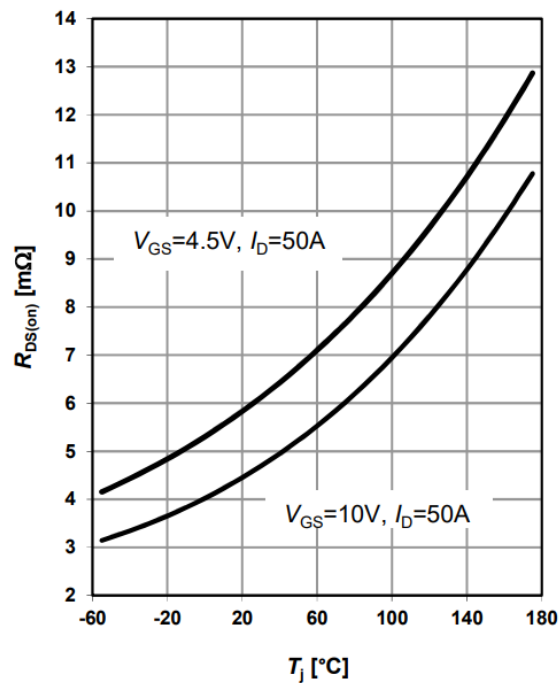
parameter: T_j



8 典型漏源导通电阻

$$R_{DS(on)} = f(T_j);$$

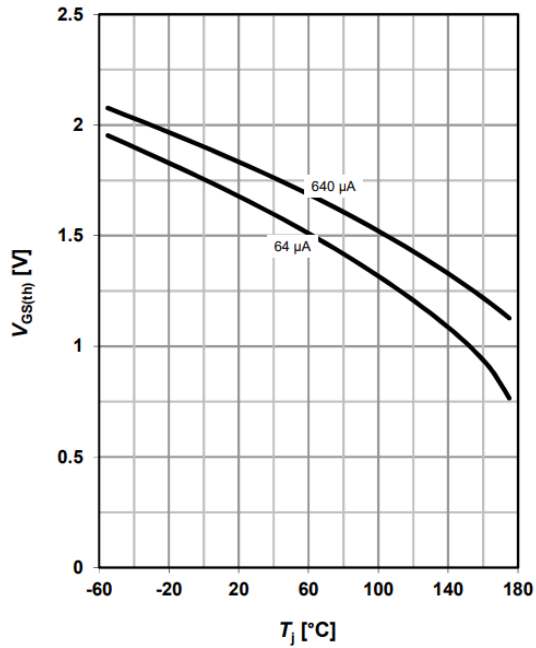
parameter: I_D, V_{GS}



9 典型栅极阈值电压

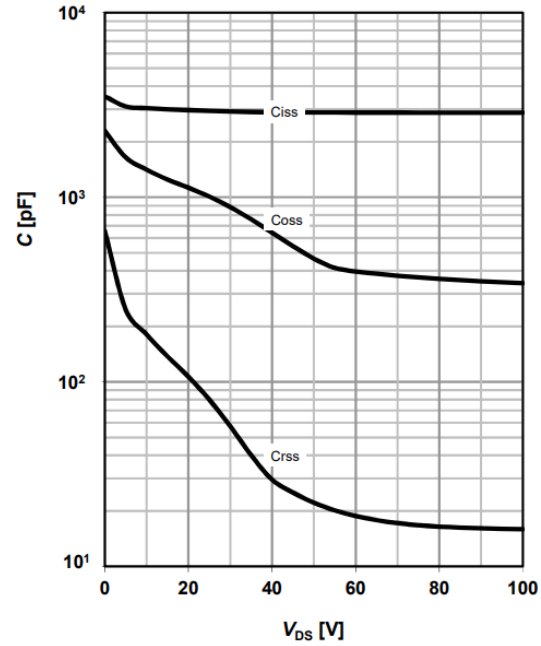
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



10 典型电容值

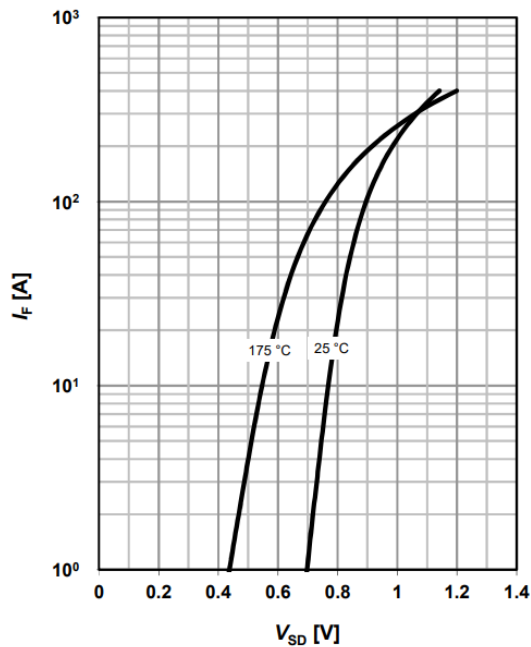
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



11 典型二极管正向导通特性

$$I_F = f(V_{SD})$$

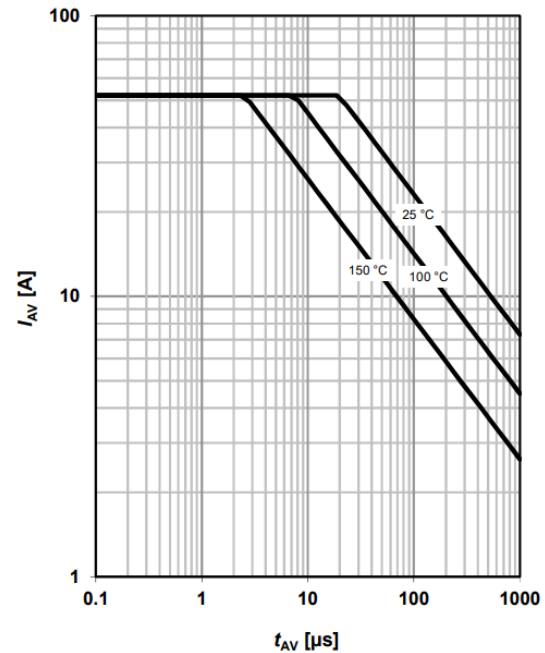
parameter: T_j



12 典型雪崩特性

$$I_{AS} = f(t_{AV})$$

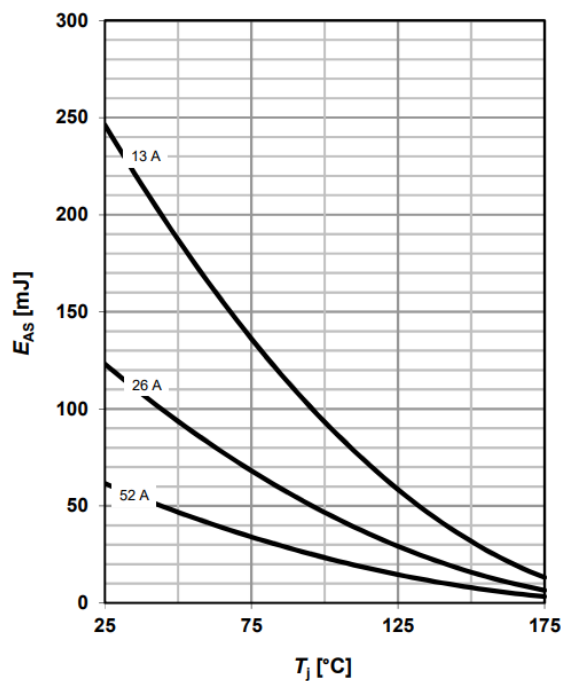
parameter: $T_{j(start)}$



13 典型雪崩能量

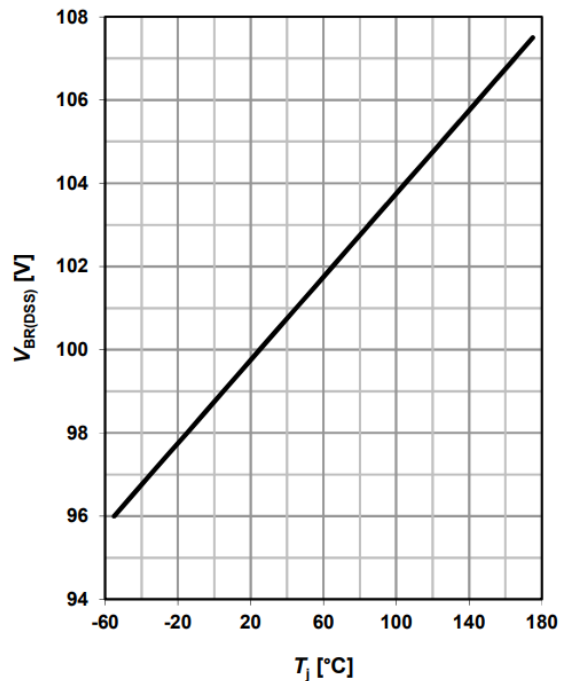
$$E_{AS} = f(T_j)$$

parameter: I_D



14 漏源击穿电压

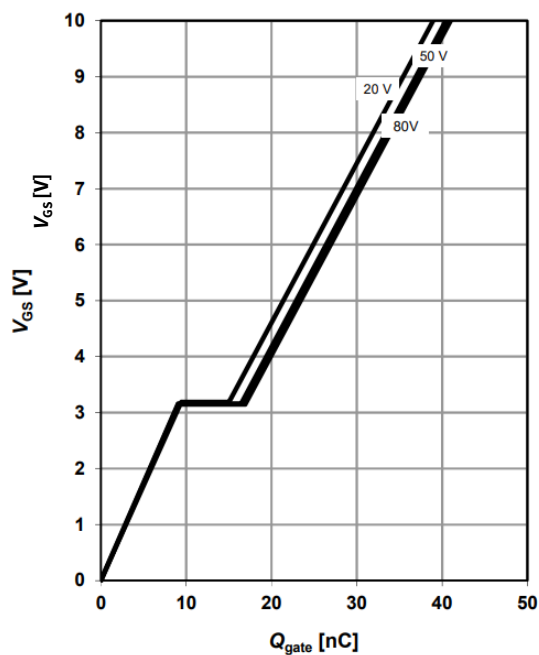
$$V_{BR(DSS)} = f(T_j); I_D = 1\text{ mA}$$



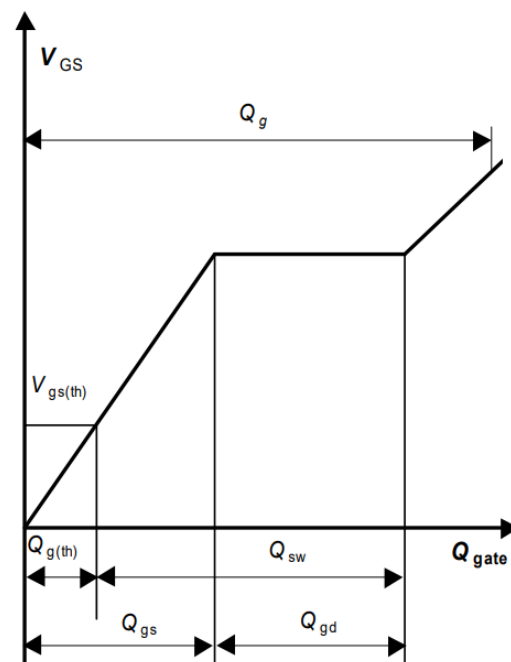
15 典型栅极电荷

$$V_{GS} = f(Q_{gate}); I_D = 20\text{ A pulsed}$$

parameter: V_{DD}



16 栅极充电波形



Technical drawing of a square flange component with dimensions and tolerances:

- Top View:**
 - Overall width: 5.15 ± 0.1
 - Overall height: 6.44 ± 0.1
 - Distance from center to mounting hole center: 0.48 ± 0.1
 - Mounting hole diameter: $\varnothing 0.25$
 - Central hole diameter: 1.27
 - Flange thickness: 0.13 ± 0.1
 - Surface texture symbol: $R_{\text{INDEX MARKING}}$
 - Dimensional callouts: 1), 2), 3)
- Side View:**
 - Flange thickness: 0.25 ± 0.1
- Cross-sectional View:**
 - Inner diameter: 4.3 ± 0.1
 - Outer diameter: 5.48 ± 0.1
 - Mounting hole diameter: $\varnothing 0.25$
 - Flange thickness: 0.9 ± 0.1
 - Distance from center to mounting hole center: 0.44 ± 0.1
 - Mounting hole diameter: $\varnothing 0.25$
 - Surface texture symbol: $R_{\text{INDEX MARKING}}$

2021-06-18

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修订记录

Version	Date	Changes
Revision 1.0	2021-05-14	Final Data Sheet
Revision 1.1	2021-06-18	Datasheet file name updated



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